MMBT3906LT1

Preferred Device

General Purpose Transistor

PNP Silicon

ON Semiconductor®

Features

- Pb−Free Packages are Available

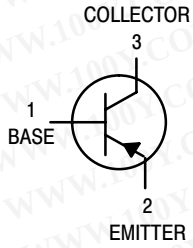
MAXIMUM RATINGS

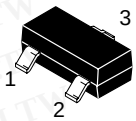
Rating	Symbol	Value	Unit
Collector−Emitter Voltage	V_{CEO}	−40	Vdc
Collector−Base Voltage	V_{CBO}	−40	Vdc
Emitter−Base Voltage	V_{EBO}	−5.0	Vdc
Collector Current − Continuous	I_C	−200	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR−5 Board (Note 1) T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction−to−Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T_J, T_{stg}	−55 to +150	°C

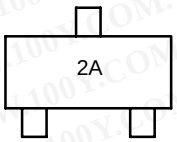
1. FR−5 = 1.0 × 0.75 × 0.062 in.
2. Alumina = 0.4 × 0.3 × 0.024 in. 99.5% alumina.





SOT−23 (TO−236)
CASE 318
Style 6

MARKING DIAGRAM



2A = Specific Device Code

ORDERING INFORMATION

Device	Package	Shipping†
MMBT3906LT1	SOT−23	3000 / Tape & Reel
MMBT3906LT1G	SOT−23	3000 / Tape & Reel
MMBT3906LT3	SOT−23	10000 / Tape & Reel
MMBT3906LT3G	SOT−23	10000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector−Emitter Breakdown Voltage (I_C = −1.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	−40	—	Vdc
Collector−Base Breakdown Voltage (I_C = −10 μAdc, I_E = 0)	$V_{(BR)CBO}$	−40	—	Vdc
Emitter−Base Breakdown Voltage (I_E = −10 μAdc, I_C = 0)	$V_{(BR)EBO}$	−5.0	—	Vdc
Base Cutoff Current (V_{CE} = −30 Vdc, V_{EB} = −3.0 Vdc)	I_{BL}	—	−50	nAdc
Collector Cutoff Current (V_{CE} = −30 Vdc, V_{EB} = −3.0 Vdc)	I_{CEX}	—	−50	nAdc
ON CHARACTERISTICS (Note 3)				
DC Current Gain	H_{FE}			—
(I_C = −0.1 mAdc, V_{CE} = −1.0 Vdc)		60	—	
(I_C = −1.0 mAdc, V_{CE} = −1.0 Vdc)		80	—	
(I_C = −10 mAdc, V_{CE} = −1.0 Vdc)		100	300	
(I_C = −50 mAdc, V_{CE} = −1.0 Vdc)		60	—	
(I_C = −100 mAdc, V_{CE} = −1.0 Vdc)		30	—	
Collector−Emitter Saturation Voltage	$V_{CE(sat)}$			Vdc
(I_C = −10 mAdc, I_B = −1.0 mAdc)		—	−0.25	
(I_C = −50 mAdc, I_B = −5.0 mAdc)		—	−0.4	
Base−Emitter Saturation Voltage	$V_{BE(sat)}$			Vdc
(I_C = −10 mAdc, I_B = −1.0 mAdc)		−0.65	−0.85	
(I_C = −50 mAdc, I_B = −5.0 mAdc)		—	−0.95	
SMALL−SIGNAL CHARACTERISTICS				
Current−Gain — Bandwidth Product (I_C = −10 mAdc, V_{CE} = −20 Vdc, f = 100 MHz)	f_T	250	—	MHz
Output Capacitance (V_{CB} = −5.0 Vdc, I_E = 0, f = 1.0 MHz)	C_{obo}	—	4.5	pF
Input Capacitance (V_{EB} = −0.5 Vdc, I_C = 0, f = 1.0 MHz)	C_{ibo}	—	10	pF
Input Impedance (I_C = −1.0 mAdc, V_{CE} = −10 Vdc, f = 1.0 kHz)	h_{ie}	2.0	12	kΩ
Voltage Feedback Ratio (I_C = −1.0 mAdc, V_{CE} = −10 Vdc, f = 1.0 kHz)	h_{re}	0.1	10	X 10^{-4}
Small−Signal Current Gain (I_C = −1.0 mAdc, V_{CE} = −10 Vdc, f = 1.0 kHz)	h_{fe}	100	400	—
Output Admittance (I_C = −1.0 mAdc, V_{CE} = −10 Vdc, f = 1.0 kHz)	h_{oe}	3.0	60	μmhos
Noise Figure (I_C = −100 μAdc, V_{CE} = −5.0 Vdc, R_S = 1.0 kΩ, f = 1.0 kHz)	NF	—	4.0	dB
SWITCHING CHARACTERISTICS				
Delay Time	(V_{CC} = −3.0 Vdc, V_{BE} = 0.5 Vdc, I_C = −10 mAdc, I_{B1} = −1.0 mAdc)	t_d	—	35	ns
Rise Time		t_r	—	35	
Storage Time	(V_{CC} = −3.0 Vdc, I_C = −10 mAdc, I_{B1} = I_{B2} = −1.0 mAdc)	t_s	—	225	ns
Fall Time		t_f	—	75	

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

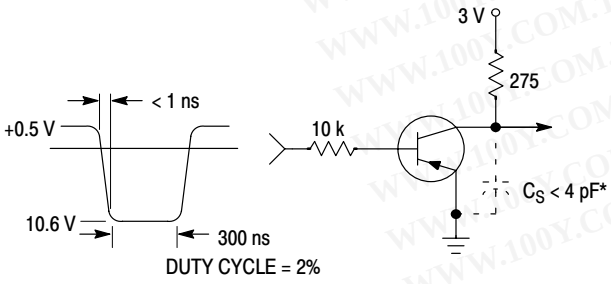


Figure 1. Delay and Rise Time Equivalent Test Circuit

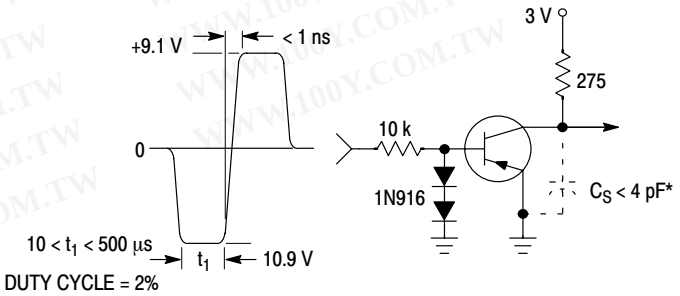


Figure 2. Storage and Fall Time Equivalent Test Circuit

* Total shunt capacitance of test jig and connectors

TYPICAL TRANSIENT CHARACTERISTICS

T_J = 25°C
T_J = 125°C

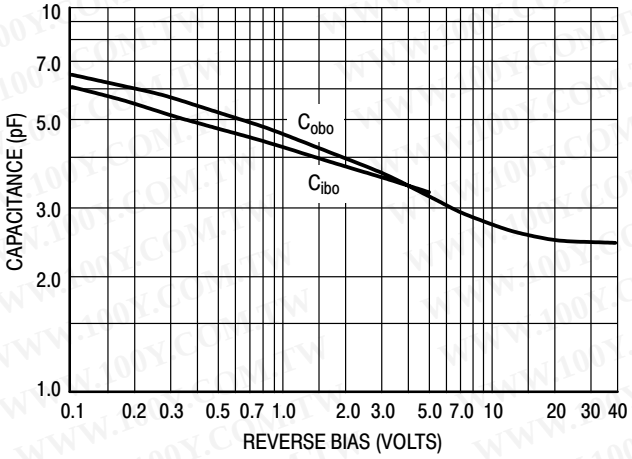


Figure 3. Capacitance

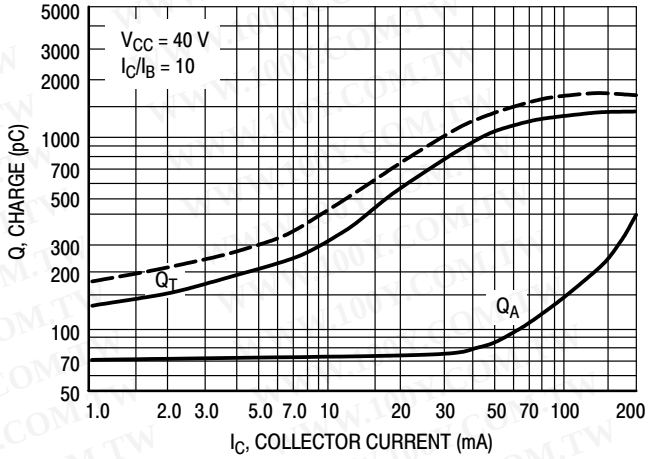


Figure 4. Charge Data

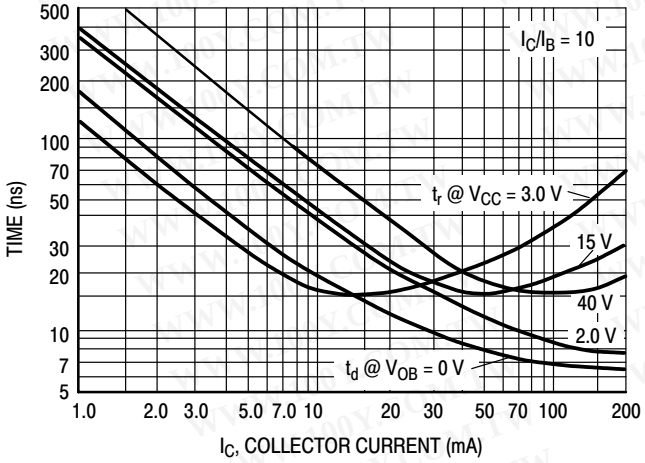


Figure 5. Turn−On Time

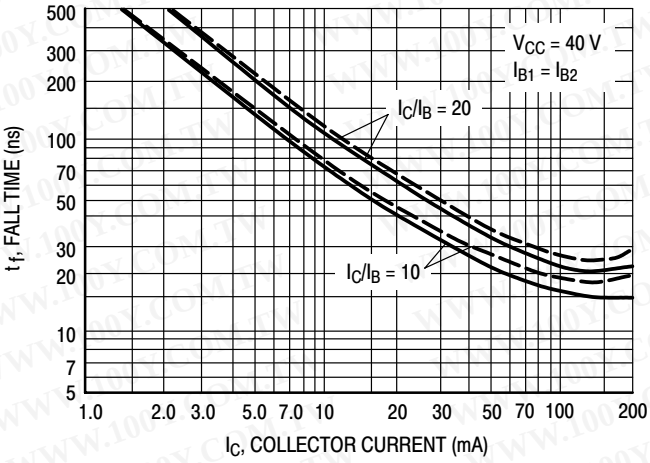


Figure 6. Fall Time

TYPICAL AUDIO SMALL−SIGNAL CHARACTERISTICS
NOISE FIGURE VARIATIONS

(V_{CE} = −5.0 Vdc, T_A = 25°C, Bandwidth = 1.0 Hz)

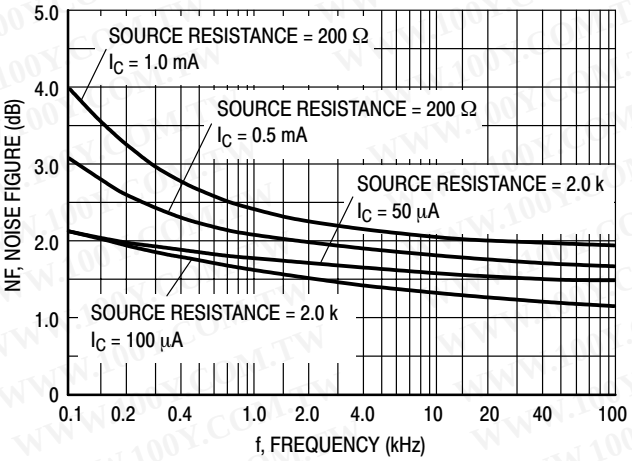


Figure 7.

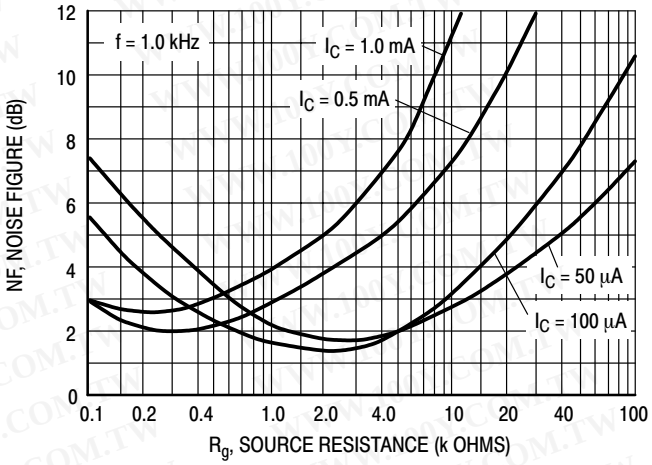


Figure 8.

h PARAMETERS

(V_{CE} = −10 Vdc, f = 1.0 kHz, T_A = 25°C)

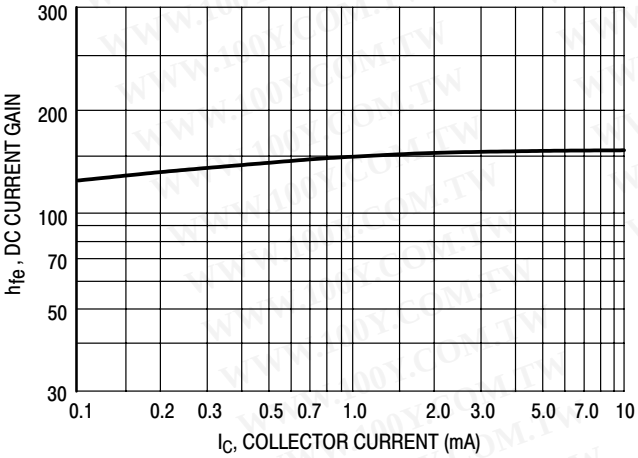


Figure 9. Current Gain

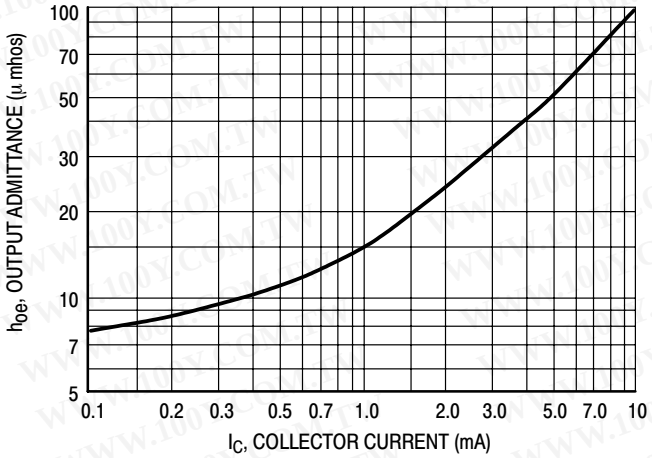


Figure 10. Output Admittance

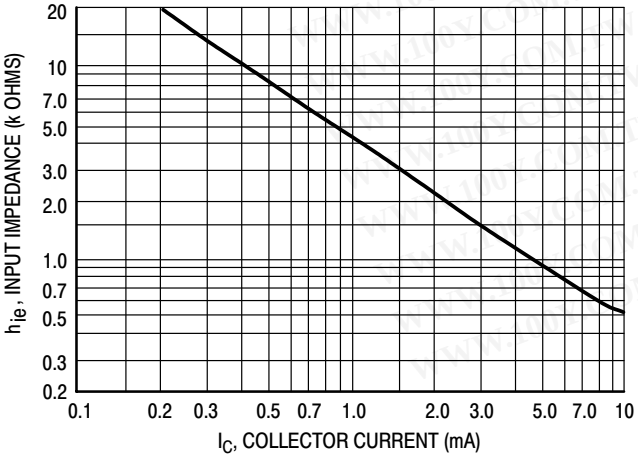


Figure 11. Input Impedance

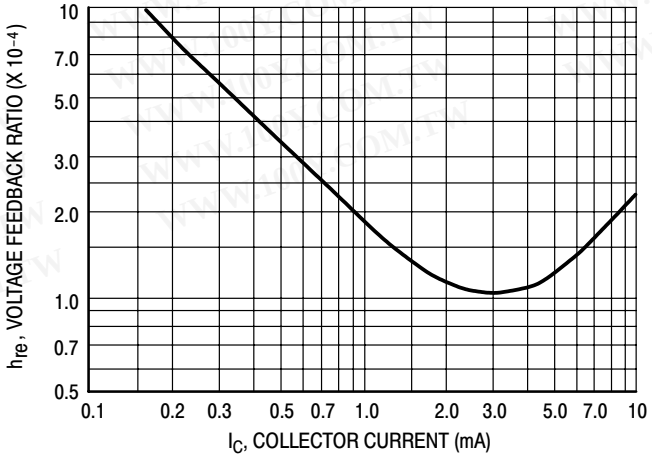


Figure 12. Voltage Feedback Ratio

TYPICAL STATIC CHARACTERISTICS

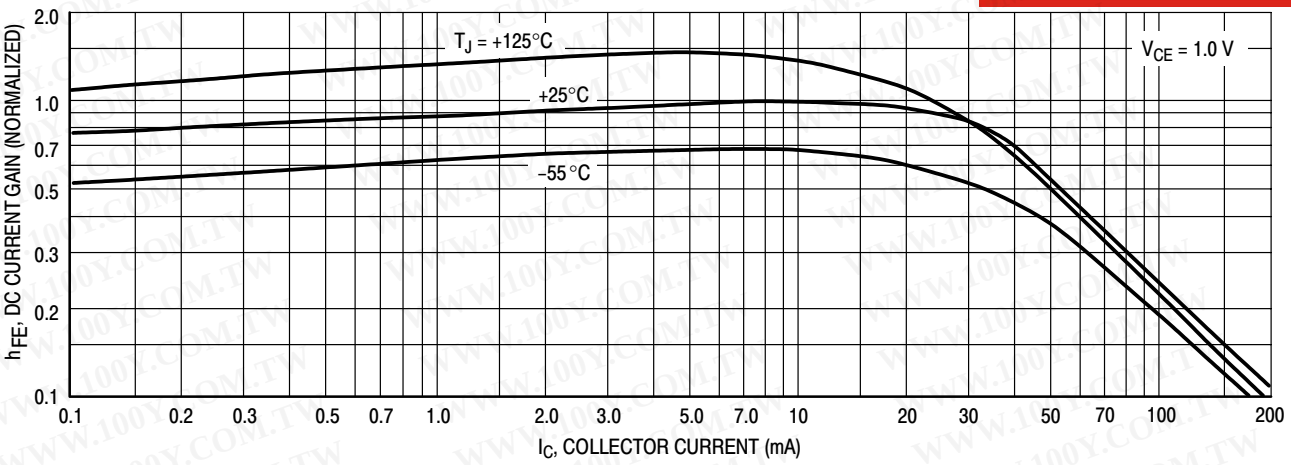


Figure 13. DC Current Gain

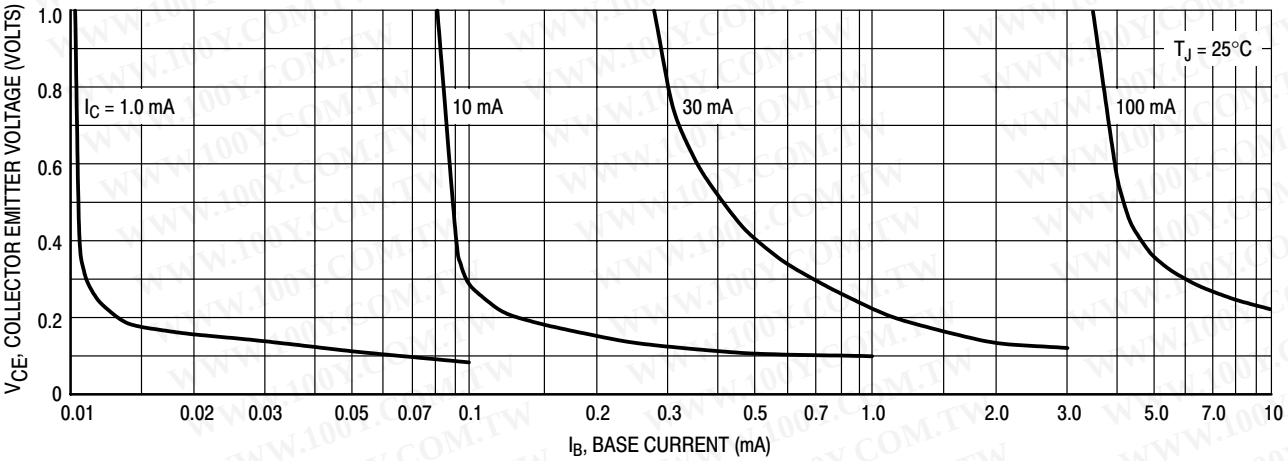


Figure 14. Collector Saturation Region

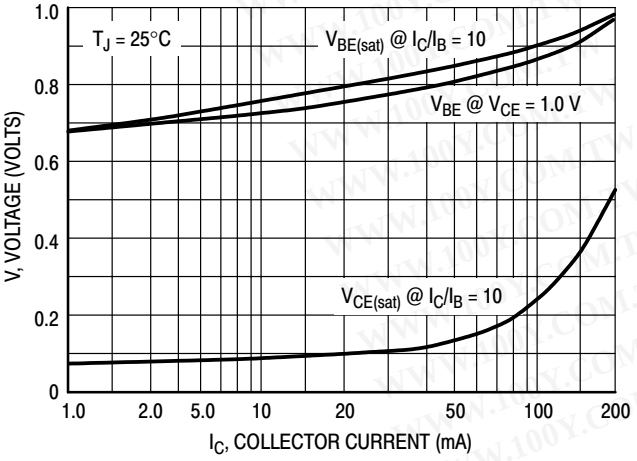


Figure 15. “ON” Voltages

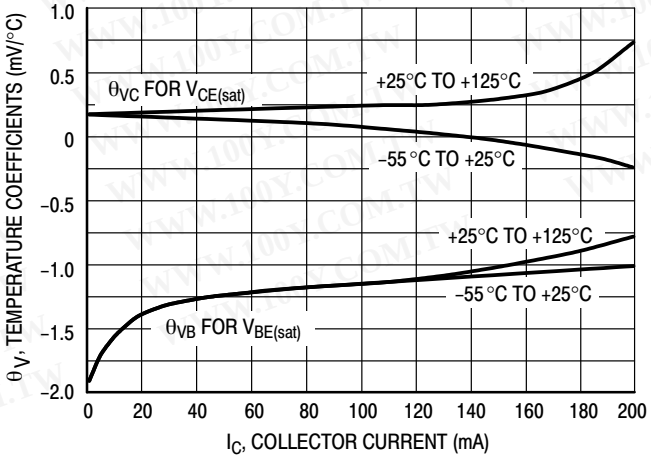
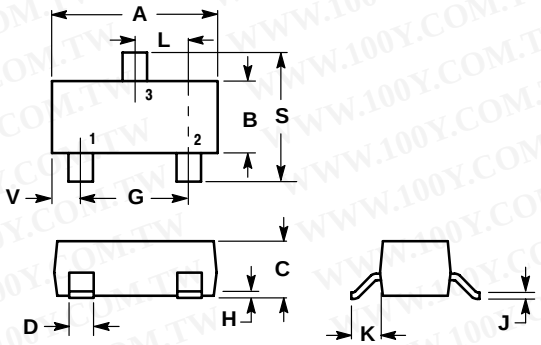


Figure 16. Temperature Coefficients

PACKAGE DIMENSIONS

SOT−23 (TO−236)
CASE 318−08
ISSUE AH



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318−03 AND −07 OBSOLETE, NEW STANDARD 318−08.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

SOLDERING FOOTPRINT*

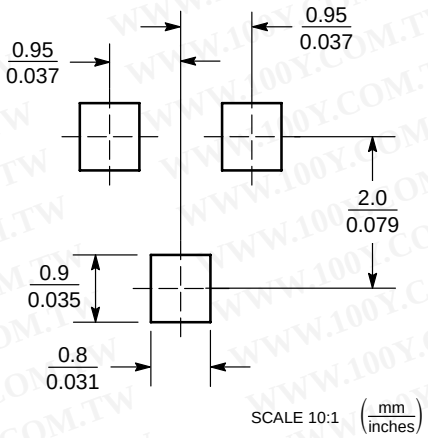


Figure 17. SOT−23

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.